reescale Semiconductor

Technical Data

RF Power LDMOS Transistor

N-Channel Enhancement-Mode Lateral MOSFET

RF power transistor suitable for industrial heating applications operating at 2450 MHz. Device is capable of both CW and pulse operation.

- Typical CW Performance at 2450 MHz, V_{DD} = 28 Vdc, I_{DQ} = 1200 mA, P_{out} = 140 W

Power Gain — 13.2 dB Drain Efficiency — 45%

 Capable of Handling 10:1 VSWR, @ 28 Vdc, 2390 MHz, 140 W CW Output Power

Features

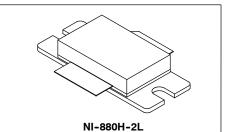
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- In Tape and Reel. R5 Suffix = 50 Units per 56 mm Tape Width, 13-inch Reel.

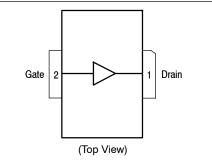
Document Number: MHT1000H Rev. 0, 5/2014

RoHS

MHT1000HR5

2450 MHz, 140 W CW, 28 V INDUSTRIAL HEATING, RUGGED RF POWER LDMOS TRANSISTOR





Note: The backside of the package is the source terminal for the transistor.

Figure 1. Pin Connections

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-0.5, +68	Vdc
Gate-Source Voltage	V _{GS}	-0.5, +12	Vdc
Storage Temperature Range	T _{stg}	- 65 to +150	°C
Case Operating Temperature	T _C	150	°C
Operating Junction Temperature (1,2)	TJ	225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value ^(2,3)	Unit
Thermal Resistance, Junction to Case Case Temperature 82°C, 140 W CW	R_{\thetaJC}	0.29	°C/W

1. Continuous use at maximum temperature will affect MTTF.

 MTTF calculator available at <u>http://www.freescale.com/rf</u>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

 Refer to AN1955, Thermal Measurement Methodology of RF Power Amplifiers. Go to <u>http://www.freescale.com/rf</u>. Select Documentation/Application Notes - AN1955.





Table 3. ESD Protection Characteristics

Test Methodology			Class				
Human Body Model (per JESD22-A114)	1C						
Machine Model (per EIA/JESD22-A115)				A			
Charge Device Model (per JESD22-C101)				11			
Table 4. Electrical Characteristics $(T_A = 25^{\circ}C \text{ unless otherwise } r$	oted)						
Characteristic	Symbol	Min	Тур	Max	Unit		
Off Characteristics							
Zero Gate Voltage Drain Leakage Current (V _{DS} = 68 Vdc, V _{GS} = 0 Vdc)	I _{DSS}		_	10	μAdc		
Zero Gate Voltage Drain Leakage Current (V _{DS} = 28 Vdc, V _{GS} = 0 Vdc)	I _{DSS}	—	_	1	μAdo		
Gate-Source Leakage Current (V _{GS} = 5 Vdc, V _{DS} = 0 Vdc)	I _{GSS}		_	500	nAdo		
On Characteristics							
Gate Threshold Voltage (V _{DS} = 10 Vdc, I _D = 300 μAdc)	V _{GS(th)}	1	2	3	Vdc		
Gate Quiescent Voltage (V_{DD} = 28 Vdc, I_D = 1300 mAdc, Measured in Functional Test)	V _{GS(Q)}	2	2.8	4	Vdc		
Drain-Source On-Voltage (V _{GS} = 10 Vdc, I _D = 3 Adc)	V _{DS(on)}	0.1	0.21	0.3	Vdc		
Dynamic Characteristics ⁽¹⁾			•	•			
Reverse Transfer Capacitance (V _{DS} = 28 Vdc ± 30 mV(rms)ac @ 1 MHz, V _{GS} = 0 Vdc)	C _{rss}		2	_	pF		

Functional Tests (in Freescale Test Firsture, 50 onm system) $V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 1300 \text{ mA}$, $P_{out} = 28 \text{ W Avg.}$, f = 2390 MHz, 2-Carrier W-CDMA, 3.84 MHz Channel Bandwidth Carriers. ACPR measured in 3.84 MHz Channel Bandwidth @ ±5 MHz Offset. IM3 measured in 3.84 MHz Bandwidth @ ±10 MHz Offset. Input Signal PAR = 8.5 dB @ 0.01% Probability on CCDF.

Power Gain	G _{ps}	13	15.2	17	dB
Drain Efficiency	ηD	23	25	—	%
Intermodulation Distortion	IМЗ	—	-37	-35	dBc
Adjacent Channel Power Ratio	ACPR	—	-40	-38	dBc
Input Return Loss	IRL	—	-15	—	dB

1. Part internally matched both on input and output.

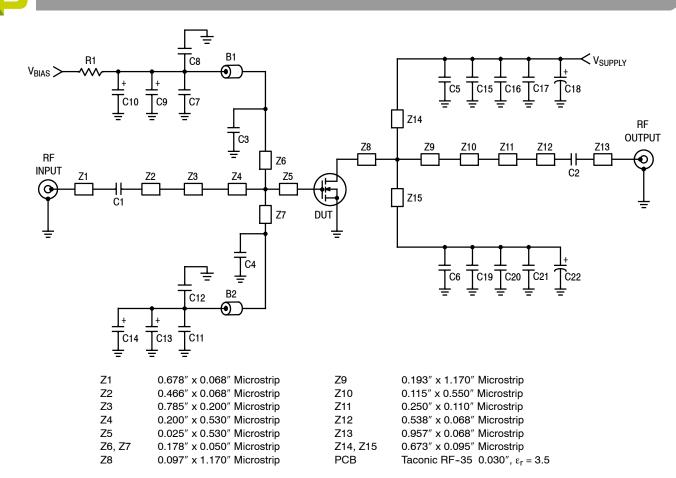
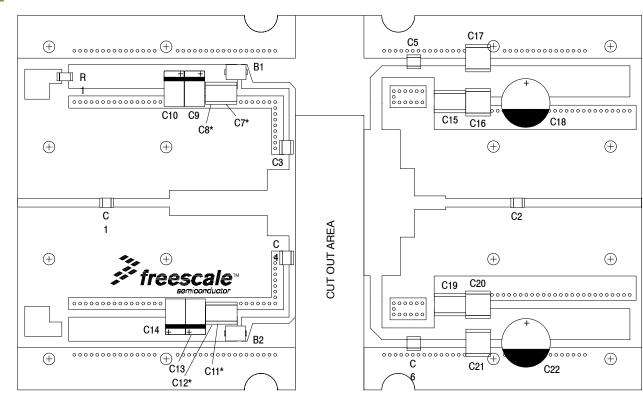


Figure 1. MHT1000HR5 Test Circuit Schematic — 2450 MHz

Table 5. MHT1000HR5 Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer	
B1, B2	47 Ω, 100 MHz Short Ferrite Beads, Surface Mount	2743019447	Fair-Rite	
C1, C2, C3, C4, C5, C6	5.6 pF Chip Capacitors	ATC600B5R6BT500XT	ATC	
C7, C11	0.01 µF, 100 V Chip Capacitors	C1825C103J1RAC	Kemet	
C8, C12, C15, C19	2.2 µF, 50 V Chip Capacitors	C1825C225J5RAC	Kemet	
C9, C13	22 μF, 25 V Tantalum Capacitors	T491D226M025AT	Kemet	
C10, C14	47 μF, 16 V Tantalum Capacitors	T491D476K016AT	Kemet	
C16, C17, C20, C21	10 μF, 50 V Chip Capacitors	GRM55DR61H106KA88B	Murata	
C18, C22	220 µF, 50 V Electrolytic Capacitors	2222-150-95102	Vishay	
R1	240 Ω, 1/4 W Chip Resistor	CRC12062400FKEA	Vishay	

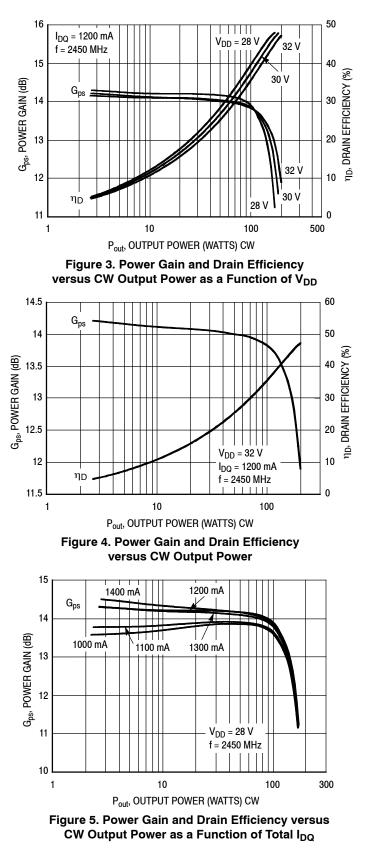


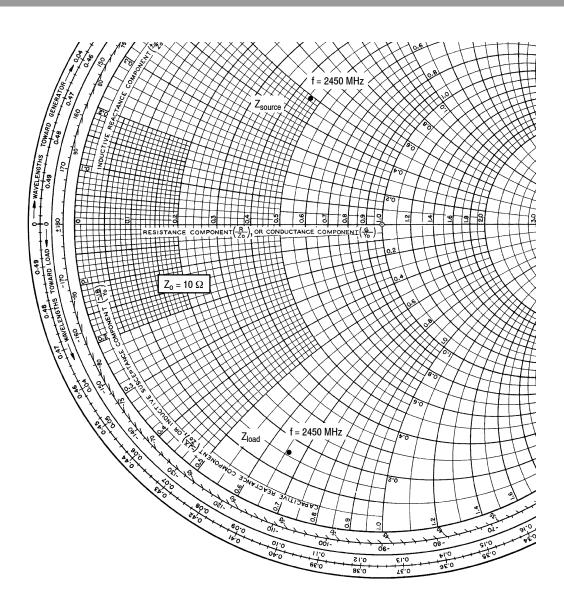
* Stacked

Figure 2. MHT1000HR5 Test Circuit Component Layout



TYPICAL CHARACTERISTICS — 2450 MHz





 V_{DD} = 28 Vdc, I_{DQ} = 1200 mA, P_{out} = 140 W CW

f	Z _{source}	Z _{load}
MHz	Ω	Ω
2450	4.55 + j4.9	1.64 - j6.57

- Z_{source} = Test circuit impedance as measured from gate to ground.
- Z_{load} = Test circuit impedance as measured from drain to ground.

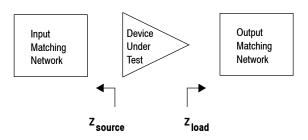
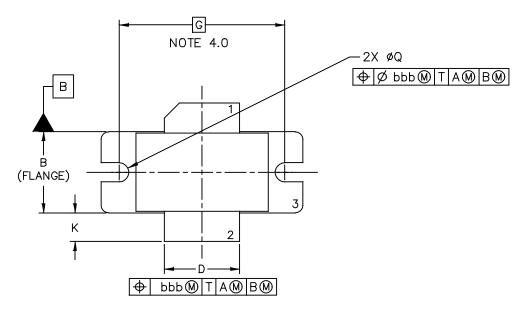
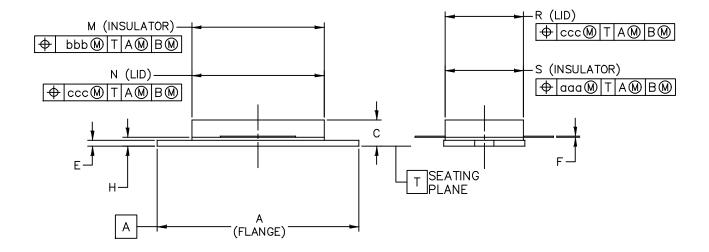


Figure 6. Series Equivalent Source and Load Impedance



PACKAGE DIMENSIONS





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TITLE:		DOCUMENT NO	: 98ARB18493C	REV: F
NI-880	CASE NUMBER	26 MAY 2011		
	STANDARD: NON-JEDEC			



NOTES:

- 1.0 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
- 2.0 CONTROLLING DIMENSION: INCH.
- 3.0 DIMENSION H IS MEASURED .030 (0.762) AWAY FROM PACKAGE BODY.
- 4.0 RECOMMENDED BOLT CENTER DIMENSION OF 1.16 (29.57) BASED ON M3 SCREW.

	IN	СН	MIL	LIMETER		INCH		М	ILLIME	TER	
DIM	MIN	MAX	MIN	MAX	DIM	MIN		MAX	MIN		MAX
A	1.335	1.345	33.91	34.16	R	.515	—	.525	13.0	8 —	13.34
В	.535	.545	13.59	13.84	S	.515	_	.525	13.0	8 —	13.34
С	.147	.200	3.73	5.08	aaa	-	.007	_	_	0.178	3 —
D	.495	.505	12.57	12.83	bbb	-	.010	_	_	0.254	4 —
E	.035	.045	0.89	1.14	ccc	-	.015	—	_	0.38′	ı —
F	.003	.006	0.08	0.15	_	-	_	_	-	_	_
G	1.100	BSC	27	.94 BSC	_	-	_	_	_	_	_
н	.057	.067	1.45	1.70	—	-	_	_	_	_	_
К	.175	.205	4.45	5.21	—	-	_	_	_	_	_
М	.872	.888	22.15	22.56	_	-	_	_	-	_	_
N	.871	.889	22.12	22.58	_	-	—	_	_	_	_
Q	ø.118	ø.138	ø3.00	ø3.51	—	-	_	_	_	_	_
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		NI-88	0		CASE	NUMBEF	R: 465	B-04		26	MAY 11
STANDARD: NON-JEDEC											



PRODUCT DOCUMENTATION AND SOFTWARE

Refer to the following resources to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers
- **Engineering Bulletins**
- EB212: Using Data Sheet Impedances for RF LDMOS Devices
- Software
- Electromigration MTTF Calculator

For Software, do a Part Number search at <u>http://www.freescale.com</u>, and select the "Part Number" link. Go to the Software & Tools tab on the part's Product Summary page to download the respective tool.

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	May 2014	Initial Release of Data Sheet



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